



#### NPN SURFACE MOUNT TRANSISTOR

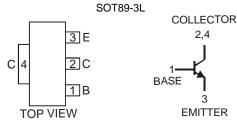
# **Features**

- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
  - "Green" Device (Note 2)

## **Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)





Schematic and Pin Configuration

# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	2.0	А

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T <sub>A</sub> = 25°C	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

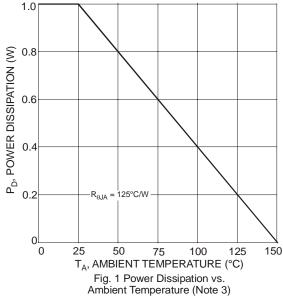
# Electrical Characteristics @TA = 25°C unless otherwise specified

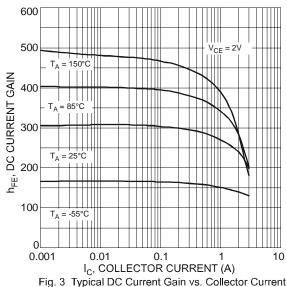
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	30		_	V	$I_C = 10\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	25	_	_	V	$I_C = 1mA, I_B = 0$	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	_	V	$I_C = 10\mu A, I_C = 0$	
Collector-Base Cutoff Current	I <sub>CBO</sub>			100	nA	$V_{CB} = 20V, I_E = 0$	
Emitter-Base Cutoff Current	I <sub>EBO</sub>		_	100	nA	$V_{EB} = 4.0V, I_{C} = 0$	
ON CHARACTERISTICS (Note 4)							
DC Current Gain	hee	200	_	400		$V_{CE} = 2.0V, I_{C} = 0.1A$	
De Current Gain	h <sub>FE</sub>	65	—	_		$V_{CE} = 2.0V, I_{C} = 1.5A$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.12	0.4	V	$I_C = 1.5A, I_B = 75mA$	
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		0.9	1.2	V	$I_C = 1.5A, I_B = 75mA$	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤		300	_	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz	
Output Capacitance	$C_{obo}$		16	_	pF	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	
SWITCHING CHARACTERISTICS							
Turn On Time	t <sub>on</sub>		70	_	ns	V 12V V 5V	
Storage Time	t <sub>stg</sub>		170	_	ns	$V_{CE} = 12V, V_{BE} = 5V,$ $I_{B1} = I_{B2} = 25\text{mA}, I_{C} = 500\text{mA}$	
Fall Time	t <sub>f</sub>	_	25	_	ns		

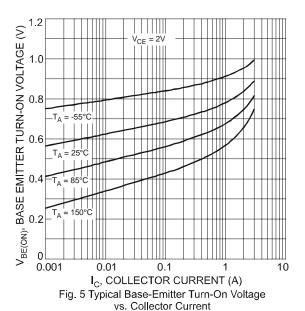
Notes:

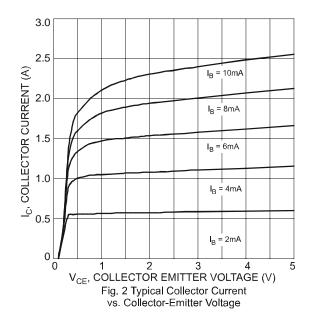
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤2%.

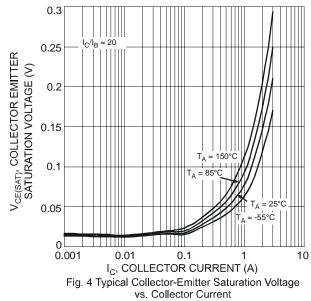


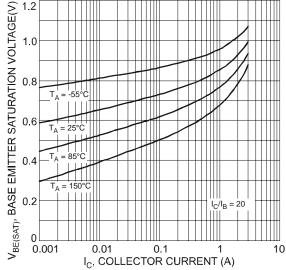




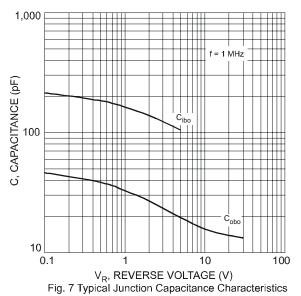


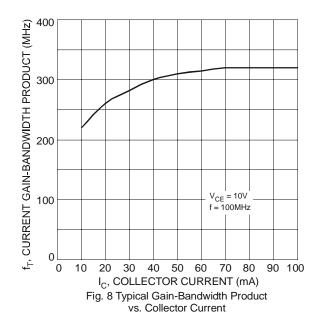










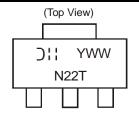


# **Ordering Information** (Note 5)

Device	Packaging	Shipping
2DD1621T-13	SOT89-3L	2500/Tape & Reel

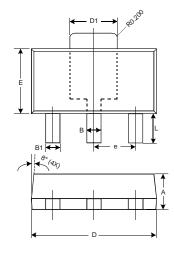
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

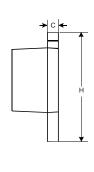
# **Marking Information**



N22T = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

# **Package Outline Dimensions**

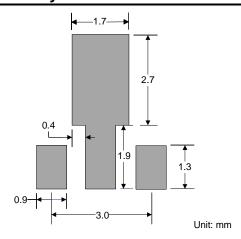




SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е	_		1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					



# **Suggested Pad Layout**



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